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Date: 5 March 2003

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From: Kenneth D. Springer

Subject: Serial No.: 09/640,754
Atty. Docket No.: SEC.747

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Comments:

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SEC.747

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of:

In-sung KIM et al.

Group Art Unit: 2823

Serial No.: 09/640,754

Examiner: Hsien Ming LEE

Filed: 18 August 2000

**SEMICONDUCTOR DEVICE
HAVING SELF-ALIGNED
CONTACT AND METHOD OF
FABRICATING THE SAME****FAX RECEIVED**

MAR -5 2003

TECHNOLOGY CENTER 2800

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Amot
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Vshort**SUPPLEMENTAL AMENDMENT**Honorable Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated 18 November 2002, and supplemental to the Amendment filed on 19 February 2003, please enter this Supplemental Amendment and amend the above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 4, line 22, with the following paragraphs:

-- FIG. 3A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a step of a first embodiment of a semiconductor device fabrication method;